TTL ISOPLANAR MEMORY 93421 / 93421A

256 × 1 - BIT FULLY DECODED RANDOM ACCESS MEMORY

LOADING

DESCRIPTION—The 93421 and 93421A are high-speed 256-bit TTL Random Access Memories with full decoding on chip. They are organized 256 words by one bit and are designed for scratchpad, buffer and distributed main memory applications. The devices have three Chip Select lines to simplify their use in larger memory systems. Address input pin locations are specifically chosen to permit maximum packaging density and for ease of PC board layout. A 3-state output is provided to drive bus organized systems and / or highly capacitive loads.

- 3-STATE OUTPUT
- REPLACEMENT FOR 54/74S200 AND EQUIVALENT DEVICES
- ORGANIZATION 256 WORDS X 1 BIT
- THREE HIGH-SPEED CHIP SELECT INPUTS
- TYPICAL READ ACCESS TIME

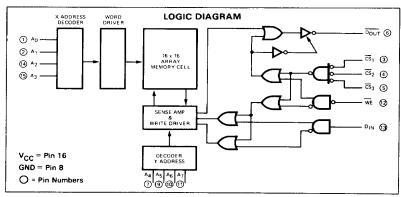
93421A	Commercial	30 n
93421	Commercial	35 n
93421	Military	35 n

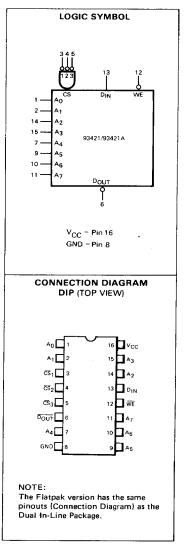
- ON CHIP DECODING
- POWER DISSIPATION 1.8 mW/BIT
- POWER DISSIPATION DECREASES WITH TEMPERATURE
- INVERTED DATA OUTPUT

PIN NAMES		(Notes a, b)
\overline{cs}_1 , \overline{cs}_2 , \overline{cs}_3	Chip Select Inputs	0.5 U.L.
$A_0 - A_7$	Address Inputs	0.5 U.L.
D _{IN}	Data Input	0.5 U.L.
DOUT	Data Output	10 U.L.
WE	Write Enable	0.5 U.L.

NOTES

- a. 1 Unit Load (U.L.) = 40 μ A HIGH / 1.6 mA LOW
- b. 10 U.L. is the output LOW drive factor. This output will sink a maximum of 16 mA at $V_{OUT} \approx 0.45$ V, and will source a minimum of 10 mA at 2.4 V.





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FAIRCHILD ISOPLANAR TTL MEMORY • 93421/93421A

FUNCTIONAL DESCRIPTION—The 93421/93421A are fully decoded 256-bit Random Access Memories organized 256 words by one bit. Word selection is achieved by means of an 8-bit address, A₀ through A₇.

Three Chip Select inputs are provided for logic flexibility. For larger memories, the fast chip select access time permits the decoding of Chip Select, \overline{CS} , from the address without increasing address access time.

The read and write operations are controlled by the state of the active LOW Write Enable ($\overline{\text{WE}}$, pin 12). With $\overline{\text{WE}}$ held LOW and the chip selected, the data at D_{IN} is written into the addressed location. To read, $\overline{\text{WE}}$ is held HIGH and the chip selected. Data in the specified location is presented at $\overline{D_{\text{OUT}}}$.

The 3-state output provides drive capability for higher speeds with high capacitive load systems. The third state (high impedance) allows bus organized systems where multiple outputs are connected to a common bus.

During writing, the output is held in the high impedance state.

TABLE I - TRUTH TABLE

		INPUTS			OUTPUT	
₹\$1	CS ₂	₹S3	WE	D _{IN}	DOUT	MODE
Н	х	х	х	×	HIGH Z	Not Selected
×	н	x	×	×	HIGH Z	Not Selected
×	x	н	×	×	HIGH Z	Not Selected
L	L	L	L	L	HIGH Z	Write "0"
L	į L	L	L	н	HIGH Z	Write "1"
L	L	L	н	×	DOUT	Read inverted data from addressed location

H = HIGH Voltage Level

HIGH Z = High Impedance

TABLE 2 - FUNCTION TABLE

FUNCTION	IN	OUTDUT			
FUNCTION	CHIP SELECT	WRITE ENABLE	OUTPUT		
Write	L	L	HIGH Z		
Read	L	н	Stored Data		
Not Selected	н	x	HIGH Z		

ABSOLUTE MAXIMUM RATINGS (above which the useful life may be impaired)

Storage Temperature

Temperature (Ambient) Under Bias

V_{CC} Pin Potential to Ground Pin

*Input Voltage (dc)

*Input Current (dc)

**Voltage Applied to Outputs (output HIGH)

Output Current (dc) (output LOW)

-65°C to +150°C -55°C to +125°C -0.5 V to +7.0 V

-0.5 V to +5.5 V -12 mA to +5.0 mA

-0.5 V to +5.50 V +20 mA

GUARANTEED OPERATING RANGES

PART NUMBER	S	SUPPLY VOLTAGE (V _{CC})						
	MIN	TYP	MAX	AMBIENT TEMPERATURE Note 4				
93421AXC, 93421XC	4.75 V	5.0 V	5.25 V	0°C to +75°C				
93421XM	4.50 V	5.0 V	5.50 V	−55°C to +125°C				

X = package type; F for Flatpak, D for Ceramic Dip, P for Plastic Dip. See Packaging Information Section for packages available on this product.

L = LOW Voltage Level

X = Don't Care (HIGH or LOW)

^{*}Either Input Voltage limit or Input Current limit is sufficient to protect the inputs.

^{**}Output Current Limit Required.

FAIRCHILD ISOPLANAR TTL MEMORY • 93421/93421A

SYMBOL PARAMETE		Б		LIMITS						
FARAMETER			MIN	TYP (Note 3)	MAX	UNITS	CONDITIONS			
v _{OL}	Output LOW \	Voltage		0.3	0.45	V	V _{CC} = MIN, I _{OL} = 16 mA			
V _{IH}	Input HIGH Vo	oltage	2.0	1.6	-	V	Guaranteed Input Logical HIGH Voltage for all Inputs			
V _{IL}	Input LOW Vo	ltage		1.5	0.85	v	Guaranteed Input Logical LOW Voltage for all Inputs			
IIL	Input LOW Cu	irrent		-530	-800	μΑ	V _{CC} = MAX, V _{IN} = 0 V			
lн	Input HIGH Cu	rrent		1.0	20	μΑ	V _{CC} = MAX, V _{IN} = 4.5 V			
OFF	Output Currer	nt (HIGH Z)			50 -50	μΑ	V _{CC} = MAX, V _{OUT} = 2.4 V V _{CC} = MAX, V _{OUT} = 0.5 V			
V _{CD}	Input Clamp D	oiode Voltage		-1.0	-1.5	٧	V _{CC} = MAX, I _{IN} = -10 mA			
cc	Power Supply	93421XC 93421AXC		90 100	124 135	mA	$T_A = +75$ °C $V_{CC} = MAX$, WE $T_A = 0$ °C Grounded, all other inp			
	Current	93421XM		90 100	117 143		$T_A = +125$ °C @ 4.5 V, see Power Supply $T_A = -55$ °C vs Temp. Curve			
v _{он}	Output HIGH	93421XC,AXC	2.4			v	I _{OH} = −10.3 mA			
- OH	Voltage	93421XM	2.4			V	I _{OH} = -5.2 mA			
os	Output Curren Short Circuit t				-100	mA	V _{CC} = MAX, Note 7			

	RISTICS: Over Guaranteed Operating Ranges, Notes 1, 2, 4,	5.6
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		9	3421A	xc		93421	xc	9	3421)	(M		
SYMBOL	CHARACTERISTIC	MIN	TYP (Note 3)	MAX	MIN	TYP (Note 3)	MAX	MIN	TYP (Note 3)	MAX	UNITS	CONDITIONS
READ MODE [†] ACS [†] ZRCS [†] AA	DELAY TIMES Chip Select Access Time Chip Select to HIGH Z Address Access Time		20 20 30	30 30 40		20 20 35	30 30 50		25 20 35	40 40 60	ns	See Test Circui and Waveforms Note 5
WRITE MODE tzws twr	DELAY TIMES Write Disable to HIGH Z Write Recovery Time INPUT TIMING REQUIREMENTS	10	20 25	35 40	10	20 25	35 40	10	20 25	45 50	ns	
tW tWSD tWHD tWSA tWHA tWSCS tWHCS	Minimum Write Pulse Width Data Set-Up Time Prior to Write Data Hold Time After Write Address Set-Up Time Address Hold Time Chip Select Set-Up Time Chip Select Hold Time	30 5 0 5 0 5	10 0 0 0 0		30 0 5 0 5 0 5	10 0 0 0 0		40 0 5 0 5 0 5	10 0 0 0 0 0		ns	See Test Circui and Waveforms Note 6
C _I	Input Capacitance Output Capacitance		2.5 5	3.5 7		2.5 5	3.5 7		2.5 5	3.5 7	pF	Measured with pulse technique

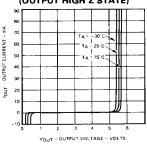
NOTES:

- 1. Conditions for testing, not shown in the Table, are chosen to guarantee operation under "worst case" conditions,
- 2. The specified LIMITS represents the "worst case" value for the parameters. Since these "worst case" values normally occur at the temperature and supply voltage extremes, additional noise immunity and guard banding can be achieved by decreasing the allowable system operating ranges.
- 3. Typical values are at $V_{CC} = 5.0 \text{ V}$, $T_A = +25^{\circ}\text{C}$, and MAX loading.
- 4. The Temperature Ranges are guaranteed with transverse air flow exceeding 400 linear feet per minute. For military range an additional requirement of a two minute warm-up. Temperature range of operation refers to case temperature for Flatpaks and ambient temperature for all other packages. Typical thermal resistance values of the package at maximum temperature are:
 - $\theta_{\rm JA}$ (Junction to Ambient) (at 400 fpm air flow) = 50°C/Watt, Ceramic DIP; 65°C/Watt, Plastic DIP; NA, Flatpak. $\theta_{\rm JA}$ (Junction to Ambient) (still air) = 90°C/Watt, Ceramic DIP; 110°C/Watt, Plastic DIP; NA, Flatpak. $\theta_{\rm JC}$ (Junction to Case) = 25°C/Watt, Ceramic DIP; 25°C/Watt, Plastic DIP; 10°C/Watt, Flatpak.
- The MAX address access time is guaranteed to be the "worst case" bit in the memory using a pseudo random testing pattern.
 t_W measured at t_{WSA} = MIN, t_{WSA} measured at t_W = MIN.
 Duration of short circuit should not exceed one second.

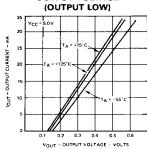
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TYPICAL ELECTRICAL CHARACTERISTICS

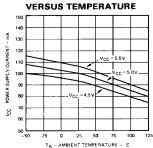
OUTPUT CURRENT VERSUS OUTPUT VOLTAGE (OUTPUT HIGH Z STATE)



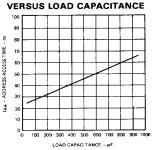
OUTPUT CURRENT VERSUS OUTPUT VOLTAGE



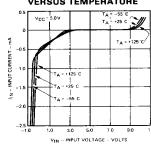
POWER SUPPLY CURRENT



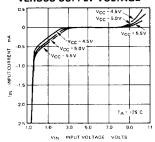
ADDRESS ACCESS TIME



INPUT CURRENT VERSUS INPUT VOLTAGE VERSUS TEMPERATURE



INPUT CURRENT VERSUS INPUT VOLTAGE VERSUS SUPPLY VOLTAGE



AC Test Load and Waveforms same as 93L420, see page 7-93, 7-94 & 7-95.